

# FFSB10120A

## Silicon Carbide Schottky Diode

**1200 V, 10 A**

### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 100 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

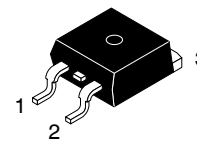
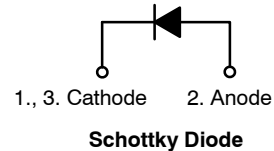
### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



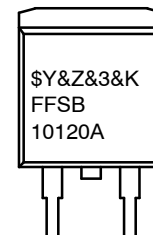
**ON Semiconductor®**

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**D<sup>2</sup>PAK-3 (TO-263, 3-LEAD)  
CASE 418AJ**

### MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FFSB10120A	= Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSB10120A

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage	1200	V	
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)	100	mJ	
I <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 164°C	10	A	
	Continuous Rectified Forward Current @ T <sub>C</sub> < 135°C	21		
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	850	A
		T <sub>C</sub> = 150°C, 10 μs	800	A
I <sub>F, SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	90	A
I <sub>F, RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	35	A
P <sub>tot</sub>	Power Dissipation	T <sub>C</sub> = 25°C	283	W
		T <sub>C</sub> = 150°C	47	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +175	°C	
	TO-247 Mounting Torque, M3 Screw	60	Ncm	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E<sub>AS</sub> of 100 mJ is based on starting T<sub>J</sub> = 25°C, L = 0.5 mH, I<sub>AS</sub> = 20 A, V = 50 V.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max	0.53	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 10 A, T <sub>C</sub> = 25°C	-	1.45	1.75	V
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 125°C	-	1.7	2.0	
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 175°C	-	2.0	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 1200 V, T <sub>C</sub> = 25°C	-	-	200	μA
		V <sub>R</sub> = 1200 V, T <sub>C</sub> = 125°C	-	-	300	
		V <sub>R</sub> = 1200 V, T <sub>C</sub> = 175°C	-	-	400	
Q <sub>C</sub>	Total Capacitive Charge	V = 800 V	-	62	-	nC
C	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	612	-	pF
		V <sub>R</sub> = 400 V, f = 100 kHz	-	58	-	
		V <sub>R</sub> = 800 V, f = 100 kHz	-	47	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSB10120A	FFSB10120A	D <sup>2</sup> PAK-3 (Pb-Free / Halogen Free)	800 / Tape & Reel

# FFSB10120A

## TYPICAL CHARACTERISTICS

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

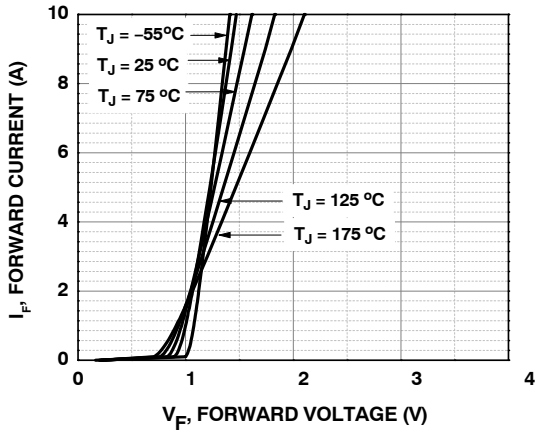


Figure 1. Forward Characteristics

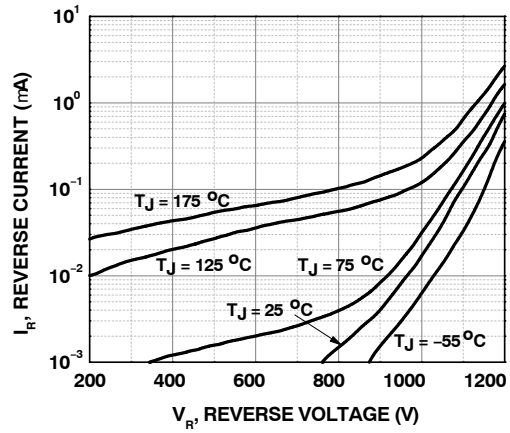


Figure 2. Reverse Characteristics

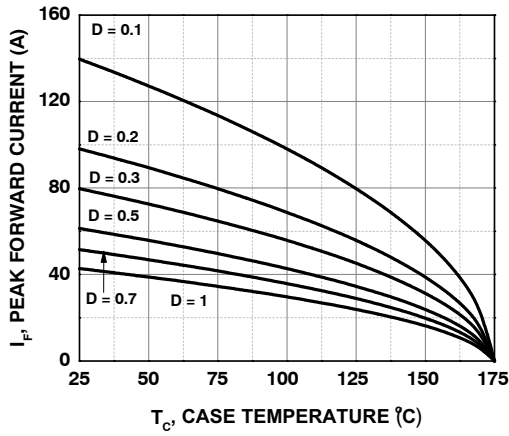


Figure 3. Current Derating

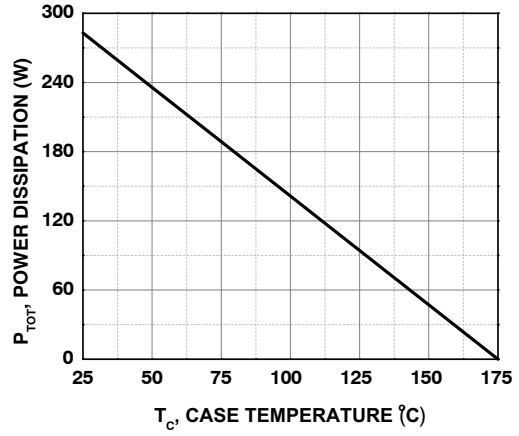


Figure 4. Power Derating

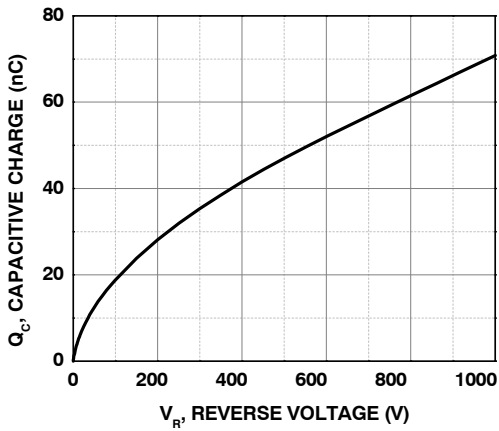


Figure 5. Capacitive Charge vs. Reverse Voltage

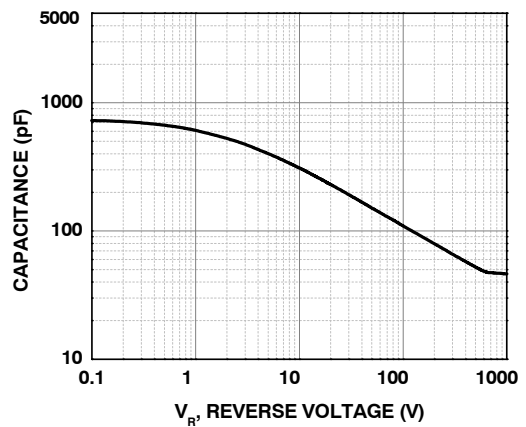


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

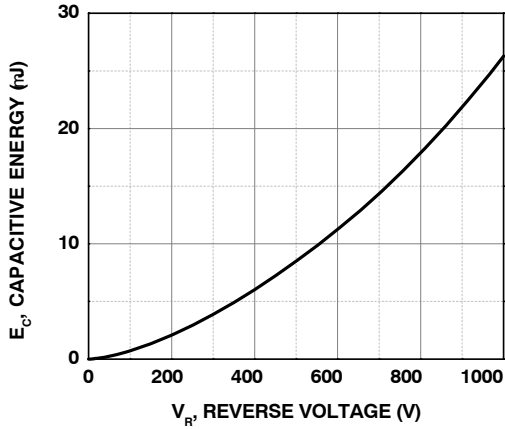


Figure 7. Capacitance Stored Energy

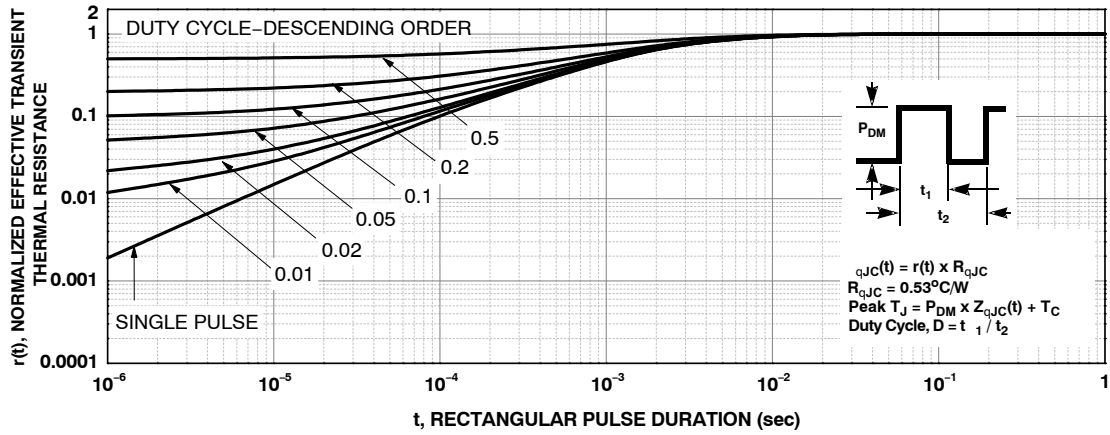


Figure 8. Junction-to-Case Transient Thermal Response Curve

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## TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$   
 $R < 0.1 \Omega$   
 $V_{DD} = 50 \text{ V}$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$   
 $Q1 = \text{IGBT (} BV_{CES} > \text{DUT } V_{R(AVL)} \text{)}$

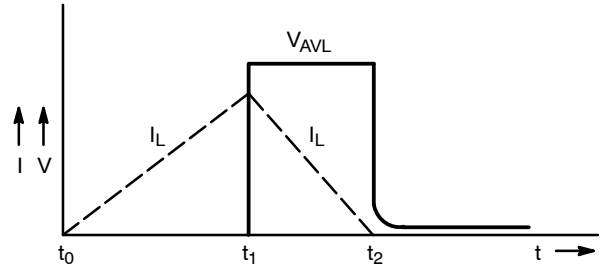
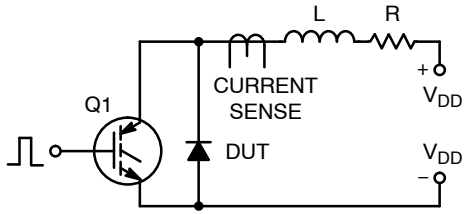
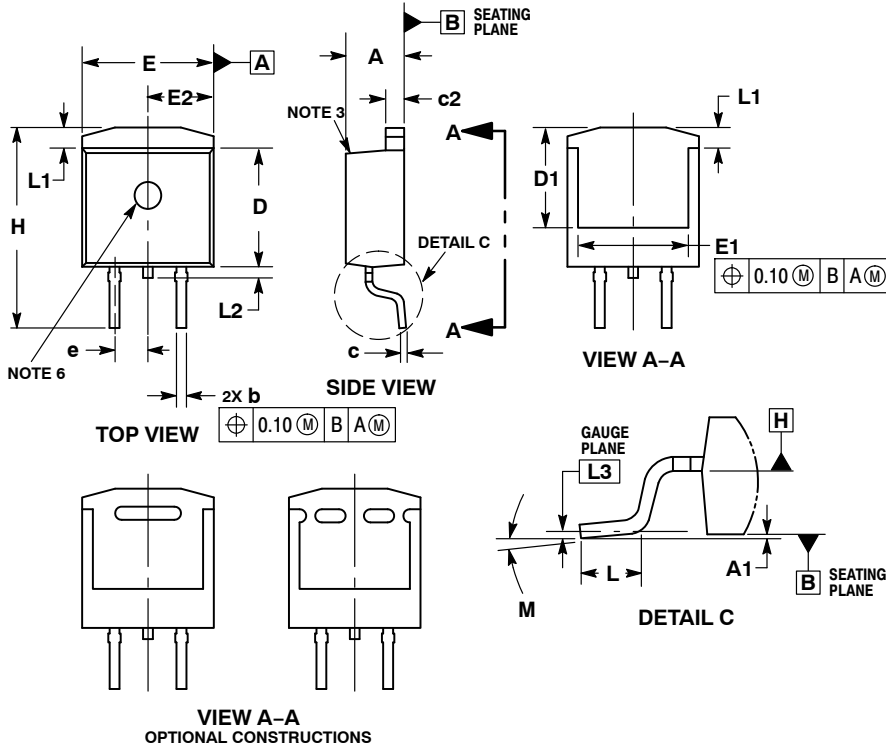


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

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## PACKAGE DIMENSIONS

**D<sup>2</sup>PAK-3 (TO-263, 3-LEAD)**  
 CASE 418AJ  
 ISSUE B

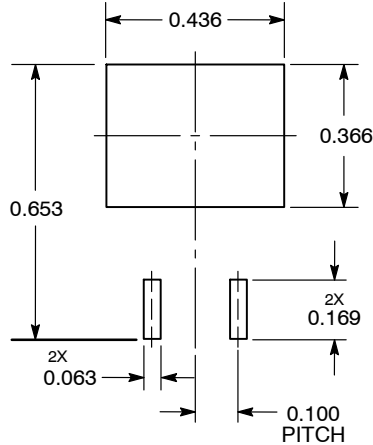


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CHAMFER OPTIONAL
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1 AND E1.
6. OPTIONAL MOLD FEATURE


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.160	0.190	4.06	4.83
A1	0.000	0.010	0.00	0.25
b	0.020	0.039	0.51	0.99
c	0.012	0.029	0.30	0.74
c2	0.045	0.065	1.14	1.65
D	0.330	0.380	8.38	9.65
D1	0.260	-----	6.60	-----
E	0.380	0.420	9.65	10.67
E1	0.245	-----	6.22	-----
e	0.100 BSC		2.54 BSC	
H	0.575	0.625	14.60	15.88
L	0.070	0.110	1.78	2.79
L1	-----	0.066	-----	1.68
L2	-----	0.070	-----	1.78
L3	0.010 BSC		0.25 BSC	
M	0°		8°	

**RECOMMENDED SOLDERING FOOTPRINT\***



DIMENSIONS: INCHES

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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